

isc N-Channel MOSFET Transistor

2SK1667

DESCRIPTION

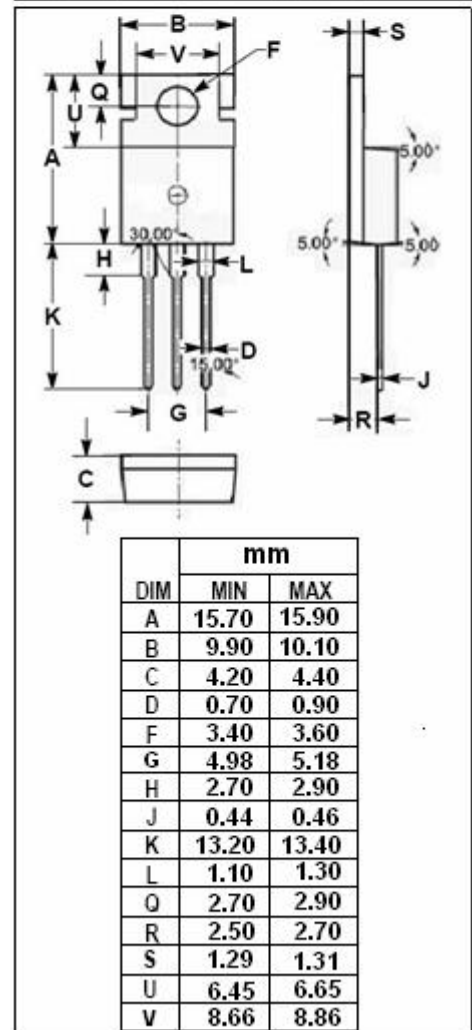
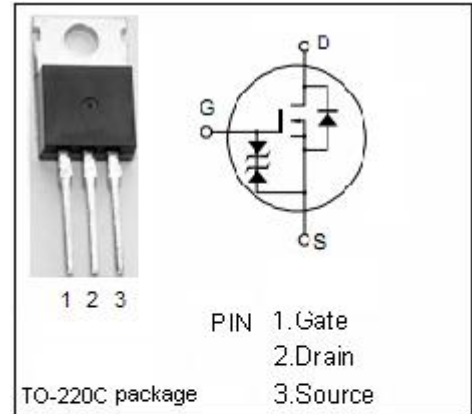
- Drain Current $-I_D = 7A @ T_C = 25^\circ C$
- Drain Source Voltage-
: $V_{DSS} = 250V(\text{Min})$
- Fast Switching Speed

APPLICATIONS

- low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator, DC-DC convertor

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS} = 0$)	250	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-continuous @ $T_C = 25^\circ C$	7	A
P_{tot}	Total Dissipation @ $T_C = 25^\circ C$	50	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



isc N-Channel Mosfet Transistor**2SK1667****• ELECTRICAL CHARACTERISTICS (T_C=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0; I _D = 10mA	250			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =10 V _{GS} ; I _D =1mA	2.0		3.0	V
R _{DS(on)}	Drain-Source On-stage Resistance	V _{GS} =10V; I _D = 4A		0.40	0.55	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±25V; V _{DS} = 0			±10	uA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =250V; V _{GS} = 0			250	uA
V _{SD}	Diode Forward Voltage	I _F =7A; V _{GS} =0		1.0		V
t _r	Rise time	V _{GS} =10V; I _D =4A; R _L =7.5 Ω		55		ns
t _{on}	Turn-on time			68		ns
t _f	Fall time			37		ns
t _{off}	Turn-off time			122		ns